

DIA2641

Low Power, High Speed, Rail-to-Rail Input and Output CMOS Amplifiers

Description

The DIA2641 is an amplifier with high supply voltage, low noise, low power consumption. The DIA2641 has a high gain-bandwidth product (GBWP) of 95 MHz and exceptionally high output current (approximately 60 mA) at low cost and with reduced power consumption when compared to existing devices with similar performance.

The DIA2641 is designed to provide optimal performance in low noise or even low voltage systems. This chip provides rail-to-rail output swing into heavy loads. Fast output slew rate ensures large peak-to-peak output swings can be maintained even at higher speeds.

It is specified over the extended industrial temperature range (-40°C to 125 °C). The operating range is from 2.7 V to 13.2 V.

Features

- AEC-Q100 qualified with the following results:
 - Device temperature grade 1: -40°C to 125°C
 - Moisture sensitivity level 1
 - HBM ESD level H3A
 - CDM ESD level C3
- Rail-to-rail input, and rail-to-rail output
- Supply voltage range: 2.7 V to 13.2 V
- Supply current (no load): 7 mA
- Low offset voltage: 13 mV (max)
- Output voltage swing 20 mV from rails

Applications

- Automotive lightings
- Body electronics
- Automotive head units
- Telematics control units
- Emergency call (eCall)
- Passive safety: brake systems

- High gain-bandwidth product:
 95 MHz when Vs = 5 V
- Slew rate (A_V = -1): 70 V/µs when V_S = 3 V, 125 V/µs when V_S = 5 V, 10 V
- Settling time: 100 ns
- Input voltage noise (100 kHz): 40 nV/√Hz
- Output short protection
- Available package: SOT23-5





Part No.	Top Marking	RoHS	TA	Pa	ckage
DIA2641ST5	YWFDA	Green	-40 to 125°C	SOT23-5	Tape & Reel,3000

If you encounter any issue in the process of using the device, please contact our customer service at marketing@dioo.com or phone us at (+86)-21-62116882. If you have any improvement suggestions regarding the datasheet, we encourage you to contact our technical writing team at docs@dioo.com. Your feedback is invaluable for us to provide a better user experience.

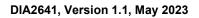


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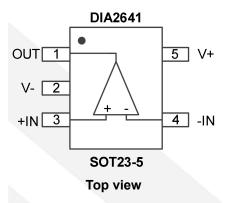
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1. Pin Assignment and Functions



Pin No.	Name	Description
1	OUT	Output
2	V-	Negative supply
3	+IN	Positive Input
4	-IN	Negative Input
5	V+	Positive supply

2. Absolute Maximum Ratings

Exceeding the maximum ratings listed under Absolute Maximum Ratings when designing is likely to damage the device permanently. Do not design to the maximum limits because long-time exposure to them might impact the device's reliability. The ratings are obtained over an operating free-air temperature range unless otherwise specified.

Symbol	Parameter	Ratings	Unit
Vs	Supply voltage	13.5	V
VIN	Input voltage	(V-)-0.5 to (V+)+0.5	V
T _{STG}	Storage temperature range	-65 to 150	°C
TJ	Junction temperature	150	°C
TL	Lead temperature range	260	°C
	Latch up	200	mA



3. Recommended Operating Condition

Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. The ratings are obtained over an operating free-air temperature range unless otherwise specified.

Symbol	Parameter	Ratings	Unit
Vs	Supply voltage	2.7 to 13.2	V
T _A	Operating temperature range	-40 to 125	°C

4. ESD Ratings

When a statically-charged person or object touches an electrostatic discharge sensitive device, the electrostatic charge might be drained through sensitive circuitry in the device. If the electrostatic discharge possesses sufficient energy, damage might occur to the device due to localized overheating.

Parameter	Standard	Value	Unit
Electrostatic discharge	Human-body model (HBM), per AEC Q100-002, all pins	±8000	V
Electrostatic discharge	Charged device model (CDM), per AEC Q100-01, all pins	±2000	V





5. Electrical Characteristics

5.1. 3 V Electrical characteristics

The typical values are obtained under these conditions unless otherwise specified: $T_A = 25^{\circ}C$, V+ = 3 V, V- = 0 V, V_{CM} = V+/2, R_L = 2 k Ω to V+/2

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Power supp	ly					
PSRR	Power supply rejection ratio	V+ = 3.0 V to 3.5 V, V _{CM} = 1.5 V		90		dB
ls	Supply current	No load		7		mA
Input						
Vos	Input offset voltage				±13	mV
M	Input common mode voltage	Low rail		0		V
V _{CM} ran	range	High rail	8	3		V
CMRR	Common mode rejection ratio	V_{CM} stepped from 0 V to 1.5 V		80		dB
Av	Open loop voltage gain	$R_L = 2 k\Omega$ to V+/2		101		dB
$\Delta V_{OS} / \Delta T$	Input offset average drift	Offset voltage average drift determined by dividing the change in V _{os} at temperature extremes by the total temperature change.		±20		μV/°C

Output

	Output abort airquit aurrant	Sourcing to V-		60		mA
lsc	Output short circuit current	Sinking from V+		70		mA
	Output ourrent	V _{OUT} = 0.5 V from V+		38		mA
lout	Output current	V _{OUT} = 0.5 V from V-		36		mA
N	Output swing high	$R_L = 2 k\Omega$ to V+/2	2.98	2.985		V
Vout	Output swing low	$R_L = 2 k\Omega$ to V+/2			15	mV

Dynamic performance

		A _V = +1, V _{OUT} = 200 mV _{PP}	78	MHz
BW	−3 dB bandwidth	A _V = +2, V _{OUT} = 200 mV _{PP}	55	MHz
		A _V = -1, V _{OUT} = 200 mV _{PP}	36	MHz
SR	Slew rate	$A_V = -1$, $V_{IN} = 2 V_{PP}$	80	V/µs
ts	Settling time	V_{OUT} = 2 V_{PP} , ±1%, 8 pF load, V_S = 5 V	100	ns
Noise perfo	ormance			

		$f = 1 \text{ kHz}, V_0 = 2 V_{PP}, A_V = -1,$		80	dB
THD	Total harmonic distortion	R_L = 100 Ω to V+ /2		80	uВ
		$f = 1 \text{ kHz}, V_{OUT} = 2 V_{PP}, A_V = -1,$	05	dB	
		R_L = 2 k Ω to V+ /2		85	uБ
en	Input-referred voltage noise	f = 100 kHz		40	nV/√Hz



5.2. 5 V Electrical Characteristics

The typical values are obtained under these conditions unless otherwise specified: $T_A = 25^{\circ}C$, V+ = 5 V,

V- = 0 V, V_{CM} = V+ /2, R_L = 2 k Ω to V+/2

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Power sup	ply					
PSRR	Power supply rejection ratio	V+ = 4 V to 6 V, V _{CM} = 2.5 V		90		dB
Is	Supply current	No load		7		mA
Input				1	1	1
Vos	Input offset voltage				±13	mV
.,	Input common mode voltage	Low rail		0		.,
V _{CM}	range	High rail		5		- V
CMRR	Common mode rejection ratio	V _{CM} stepped from 0 V to 3.5 V		80		dB
Av	Open loop voltage gain	$R_L = 2 k\Omega$ to V+/2		97		dB
ΔVos/ΔT	Input offset average drift	Offset voltage average drift determined by dividing the change in V _{os} at temperature extremes by the total temperature change.		±20		µV/°C
Output				1	I	1
-		Sourcing to V-		60		mA
I _{SC}	Output short circuit current	Sinking from V+		70		mA
		V _{OUT} = 0.5 V from V+		52		mA
Ι _{ουτ}	Output Current	V _{OUT} = 0.5 V from V-		40		mA
	Output swing high	R_L = 2 k Ω to V+/2	4.98	4.985		V
Vout	Output swing low	R_L = 2 k Ω to V+/2	15	20		mV
Dynamic p	berformance					1
		A _V = +1, V _{OUT} = 200 mV _{PP}		95		MHz
BW	−3 dB bandwidth	A _V = +2, V _{OUT} = 200 mV _{PP}		60		MHz
		A _V = -1, V _{OUT} = 200 mV _{PP}		37		MHz
SR	Slew rate	$A_V = -1$, $V_{IN} = 2 V_{PP}$		125		V/µs
ts	Settling time	V _{OUT} = 2 V _{PP} , ±1%, 8 pF load		100		ns
Noise perf	ormance					1
TUD		f = 1 kHz, V ₀ = 2 V _{PP} , A _V = -1, R _L = 100 Ω to V+ /2		80		dB
THD	Total harmonic distortion	f = 1 kHz, V _{OUT} = 2 V _{PP} , A _V = -1, R _L = 2 kΩ to V+/2		85		dB
en	Input-referred voltage noise	f = 100 kHz		40		nV/√H

Note: Specifications subject to change without notice.



5.3. 10 V Electrical Characteristics

The typical values are obtained under these conditions unless otherwise specified: $T_A = 25^{\circ}C$, V+ = 10 V, V- = 0 V, V_{CM} = V+/2 V, R_L = 2 k Ω to V+/2.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Power sup	ply			I	I		
PSRR	Power supply rejection ratio	V+ = 4 V to 6 V, V _{CM} = 0 V		90		dB	
ls	Supply current	No load		7		mA	
Input							
Vos	Input offset voltage				±13	mV	
V _{CM}	Input common mode voltage range	Low rail		0			
		High rail		10		- V	
CMRR	Common mode rejection ratio	V_{CM} stepped from 0 V to 3.5 V		80		dB	
A _V ⁽¹⁾	Open loop voltage gain	R _L = 2 kΩ		96		dB	
ΔVos/ΔT	Input offset average drift	Offset voltage average drift determined by dividing the change in V _{OS} at temperature extremes by the total temperature change.		±20		μV/°C	
Output							
1	Output short circuit current	Sourcing to V-		60		mA	
I _{SC}		Sinking from V+		60		mA	
1	Output current	V _{OUT} = 0.5 V from V+		54		mA	
IOUT		V _{OUT} = 0.5 V from V-		40		mA	
Vout	Output swing high	$R_L = 2 k\Omega$	9.98	9.985		V	
	Output swing low	$R_L = 2 k\Omega$	30			mV	
Dynamic p	performance					·	
BW	−3 dB bandwidth	A _V = +1, V _{OUT} = 200 mV _{PP}		100		MHz	
		A _V = +2, V _{OUT} = 200 mV _{PP}		63		MHz	
		A _V = -1, V _{OUT} = 200 mV _{PP}		39		MHz	
SR	Slew rate	$A_V = -1, V_I = 2 V_{PP}$		125		V/µs	
ts	Settling time	V_{OUT} = 2 V_{PP} , ±1%, 8 pFload, V_S = 5 V		110		ns	
Noise perf	ormance						
THD	Total harmonic distortion	f = 1 kHz, V _{OUT} = 2 V _{PP} , A _V = -1, R _L = 100 Ω to V+ /2		80		dB	
		$f = 1 \text{ kHz}, \text{V}_{\text{OUT}} = 2 \text{V}_{\text{PP}}, \text{A}_{\text{V}} = -1,$ $\text{R}_{\text{L}} = 2 \text{k} \Omega \text{ to } \text{V} + /2$		85		dB	
en	Input-referred voltage noise	f = 100 kHz		40		nV/√Hz	

Note:

(1) Guaranteed by design.

(2) Specifications subject to change without notice.



6. Typical Characteristics

V+ = +5 V, V- = -5 V, R_L = 2 k Ω , unless otherwise specified.

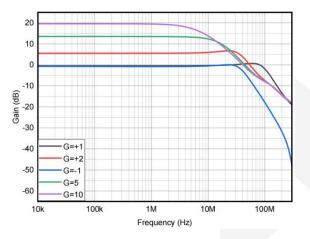


Figure 1. Closed loop gain vs. frequency for various gain

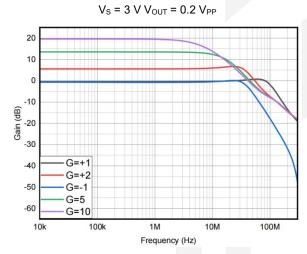
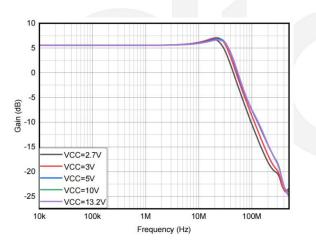
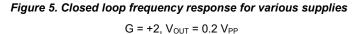


Figure 3. Closed loop gain vs. frequency for various gain V_{S} = 10 V, V_{OUT} = 0.2 V_{PP}





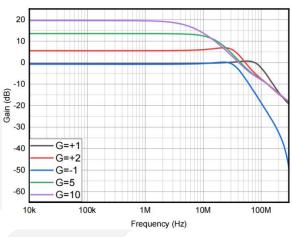


Figure 2. Closed loop gain vs. frequency for various gain

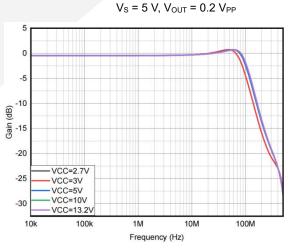
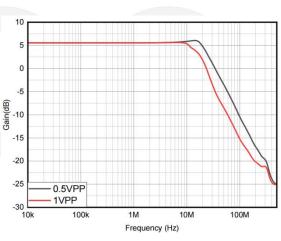
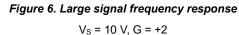


Figure 4. Closed loop frequency response for various supplies $G = +1, \, V_{OUT} = 0.2 \; V_{PP}$

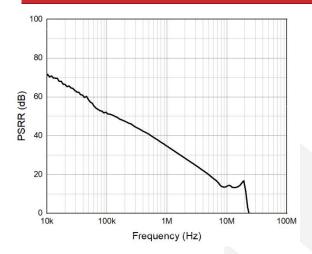




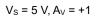
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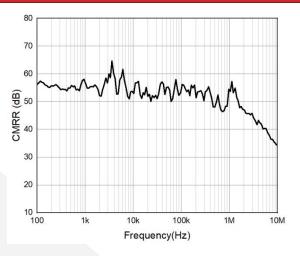


Figure 8. CMRR vs. frequency $V_S = 5 V$, $A_V = +2$

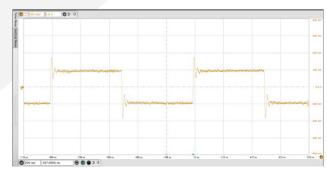


Figure 9. Small signal step response $V_S = 3 V$, $V_{OUT} = 0.2 V_{PP}$, G = 2

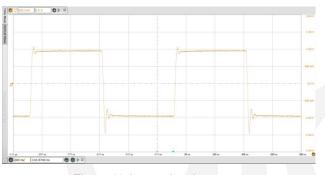
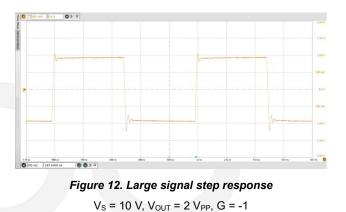




Figure 10. Small signal step response $V_S = 10 \text{ V}, V_{OUT} = 0.2 \text{ V}_{PP}, \text{ G} = 2$



7. Feature Description

The DIA2641 is designed for high-voltage, high-speed amplifier applications. The DIA2641 has low power dissipation, due to the lower supply current. The push-pull output stage offers a 54 mA output current (at 0.5 V from the supply rails); meanwhile, the total consumption of the supply current is only 7 mA. As high-performance devices, due to the subtleties of applications, it is recommended to evaluate performance under actual operating conditions to ensure the chip meets all specifications.

The DIA2641 is a high-speed, high-voltage, rail-to-rail input, rail-to-rail output Op Amp. The DIA2641 has a wide power supply voltage ranging from 2.7 V to 13.2 V. Even when supplied with 3 V, the -3 dB BW (at A_V = +1) is typically 78 MHz. Production testing guarantees that process variations will not compromise the speed.

The DIA2641 device can operate off a single supply or with dual supplies. The input CM capability of the parts (CMVR) extends down to the V- rail to simplify single supply applications. Supplies should be decoupled with low inductance, often ceramic, capacitors to ground less than 0.5 inches from the device pins. The use of a ground plane is recommended, and as in most high-speed devices, it is advisable to remove ground plane close to device-sensitive pins such as the inputs.





8. Typical Applications

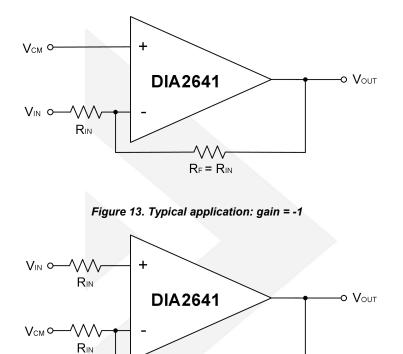
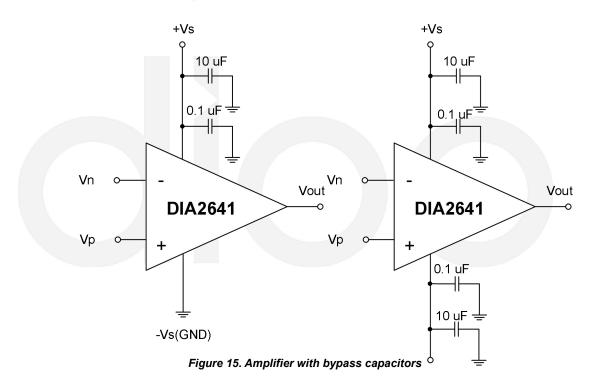
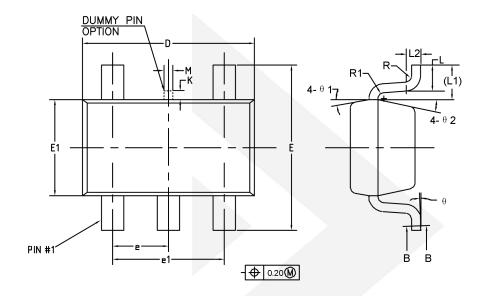


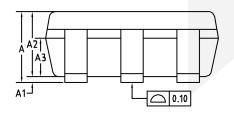
Figure 14. Typical application: gain = 2

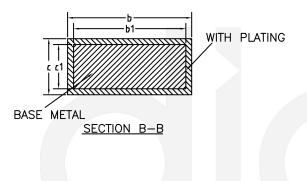




9. Physical Dimensions: SOT23-5







Common Dimensions (Units of measure = Millimeter)									
Symbol	Min	Nom	Max						
A	-	-	1.25						
A1	0	-	0.15						
A2	1.00	1.10	1.20						
A3	0.60	0.65	0.70						
b	0.36	-	0.45						
b1	0.35	0.38	0.41						
С	0.14	-	0.20						
c1	0.14	0.15	0.16						
D	2.826	2.926	3.026						
E	2.60	2.80	3.00						
E1	1.526	1.626	1.726						
е	0.90	0.95	1.00						
e1	1.80	1.90	2.00						
К	0	- /	0.25						
L	0.30	0.40	0.60						
L1	0.59 REF								
L2	0.25 BSC								
М	0.10	0.15	0.25						
R	0.05	-	0.20						
R1	0.05	-	0.20						
Θ	0°	-	8°						
Θ1	8°	10°	12°						
Θ2	10°	12°	14°						



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